

# N-Channel 80 V (D-S) Super Junction Power MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) MAX.	I <sub>D</sub> (A)	Q <sub>g</sub> (TYP.)	
80	0.0021 at V <sub>GS</sub> = 10 V	200	183 nC	

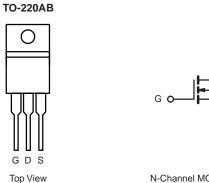
#### **FEATURES**

- Maximum 175 °C junction temperature
- 100 % R<sub>g</sub> and UIS tested



### **APPLICATIONS**

- Power supplies:
  - Uninterruptible power supplies
  - AC/DC switch-mode power supplies
  - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Battery management



View	N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b>	$(T_C = 25  ^{\circ}C, \text{ unless othe})$	rwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V <sub>DS</sub>	80	V		
Gate-Source Voltage		V <sub>GS</sub>	V <sub>GS</sub> ± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 25 °C	,	200		
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	140		
Pulsed Drain Current (t = 100 µs)		I <sub>DM</sub>	800	A	
Avalanche Current	1 0.1 ml l	I <sub>AS</sub>	190		
Single Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	1925	mJ	
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	В	300 b	W	
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	125 <sup>b</sup>	VV	
Operating Junction and Storage Temperature Range		T <sub>.I</sub> , T <sub>sta</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	2.1	°C/W	
Junction-to-Case (Drain)	R <sub>thJC</sub>	0.5		

#### Notes

- a. Duty cycle  $\leq 1 \%$ .
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).

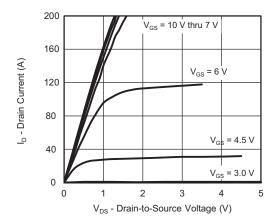
<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C	, unicos on	lei wise rioted)	1	1		
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	80	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS},I_D=250\;\mu A$	1.5	-	3.5	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$	-	1	1	μΑ
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ = 80 V, $V_{GS}$ = 0 V, $T_{J}$ = 125 °C	-	-	100	
		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$	-	-	2	mA
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	200	-	-	Α
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A	-	0.0021	0.0028	Ω
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A	-	90	-	S
Dynamic <sup>b</sup>				•		
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 50 V, f = 1 MHz	-	10500	-	pF
Output Capacitance	C <sub>oss</sub>		-	1650	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	75	-	
Total Gate Charge <sup>c</sup>	Qg		-	183		
Gate-Source Charge c	$Q_{gs}$	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	56	-	nC
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$		-	22	-	
Gate Resistance	$R_g$	f = 1 MHz		2.3		Ω
Turn-On Delay Time °	t <sub>d(on)</sub>		-	38	-	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 50 \text{ V}, R_{L} = 1.67 \Omega$	-	86	-	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 30 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	105	-	ns
Fall Time <sup>c</sup>	t <sub>f</sub>		-	42	-	
Drain-Source Body Diode Ratings ar	d Characteri	stics <sup>b</sup> (T <sub>C</sub> = 25 °C)	•			
Pulsed Current (t = 100 μs)	I <sub>SM</sub>		-	-	800	Α
Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>F</sub> = 30 A, V <sub>GS</sub> = 0 V	-	0.7	1.2	V
Reverse Recovery Time	t <sub>rr</sub>		-	118	-	ns
Peak Reverse Recovery Charge	I <sub>RM(REC)</sub>	I <sub>F</sub> = 30 A, di/dt = 100 A/μs	-	5	10	Α
Reverse Recovery Charge	Q <sub>rr</sub>		-	305	_	μC

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

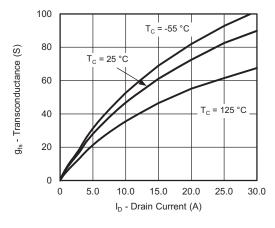
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



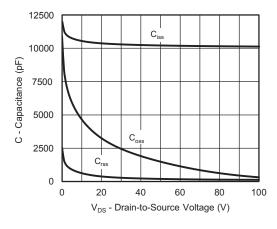
### **TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)



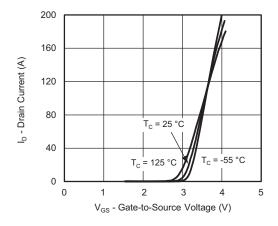
#### **Output Characteristics**



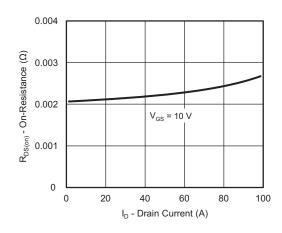
**Transconductance** 



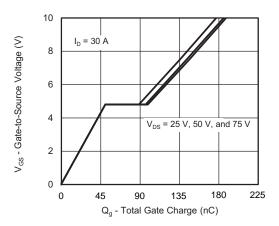
Capacitance



**Transfer Characteristics** 



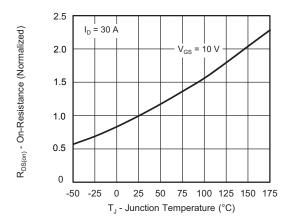
On-Resistance vs. Drain Current



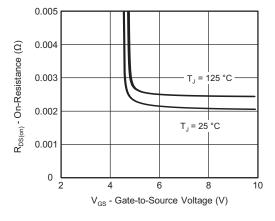
**Gate Charge** 



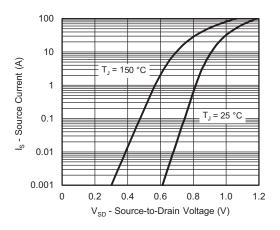
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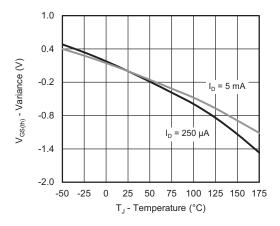
On-Resistance vs. Junction Temperature



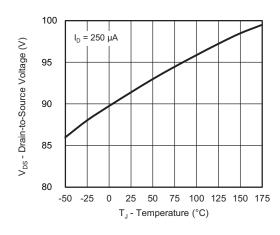
On-Resistance vs. Gate-to-Source Voltage



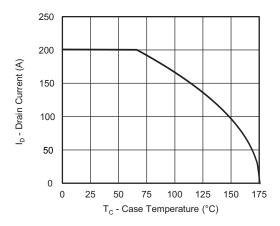
**Source Drain Diode Forward Voltage** 



**Threshold Voltage** 

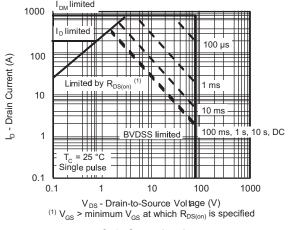


Drain Source Breakdown vs. Junction Temperature

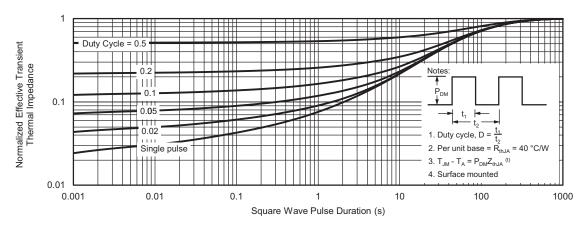


**Current De-Rating** 

### **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient





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